

**IN THE CLAIMS:**

*Please amend the claims as follows:*

1. (Currently Amended) A photomask comprising:  
  
a mask pattern formed on a transparent substrate and having a light shielding property with respect to exposing light; and  
  
a transparent portion of said transparent substrate where said mask pattern is not formed,  
  
wherein said mask pattern is surrounded by the transparent portion and includes a first pattern and a second pattern each having a line shape and having a mask enhancer structure including a phase shifter for transmitting said exposing light in an opposite phase with respect to said transparent portion and a shielding portion surrounding said phase shifter and a third pattern located adjacent to said first pattern along a direction vertical to the line direction of said first pattern, at a distance not larger than a given distance and with a transparent portion sandwiched between said first pattern and said third pattern,  
  
the outermost region in each of said first and second patterns is said shielding portion,  
  
and the outmost region of said third pattern is a shielding pattern,  
  
said phase shifter of said mask enhancer structure in said first pattern is a line-shaped pattern having a first line width with a predetermined width,  
  
said phase shifter of said mask enhancer structure in said second pattern is a line-shaped pattern having a second line width with a predetermined width,  
  
no mask pattern is located at a distance not larger than the distance between said first pattern and said third pattern, along a direction vertical to the line direction of said second pattern,

~~said first pattern is close to a third pattern included in said mask pattern at a distance not larger than a given distance with said transparent portion sandwiched therebetween, and~~

~~[[a]] said first line width of said phase shifter of the mask enhancer structure of said first pattern is smaller than [[a]] said second line width of said phase shifter of the mask enhancer structure of said second pattern.~~

2. (Original) The photomask of Claim 1, wherein each of regions of said transparent portion disposed on both sides of said second pattern has a width larger than a given dimension.

3. (Original) The photomask of Claim 2, wherein said third pattern has the mask enhancer structure or is made of a shielding portion.

4. (Original) The photomask of Claim 3, wherein said third pattern is provided with a semi-shielding portion for partially transmitting the exposing light in an identical phase with respect to said transparent portion instead of said shielding portion of the mask enhancer structure.

5. (Currently amended) The photomask of Claim 1,  
wherein said mask pattern further comprises a fourth pattern,  
~~said second pattern is close to a~~ said fourth pattern is located ~~included in said mask~~  
~~pattern at a distance not larger than said given distance with said transparent portion sandwiched~~  
~~therebetween~~ between said fourth pattern and said second pattern along a direction vertical to the  
line direction of said second pattern, and

the distance between said second pattern and said fourth pattern is larger than the distance between said first pattern and said third pattern.

6. (Original) The photomask of Claim 5, wherein each of said third pattern and said fourth pattern has the mask enhancer structure or is made of a shielding portion.

7. (Original) The photomask of Claim 6, wherein each of said third pattern and said fourth pattern is provided with a semi-shielding portion for partially transmitting the exposing light in an identical phase with respect to said transparent portion instead of said shielding portion of the mask enhancer structure.

8-9. (Cancelled)

10. (Original) The photomask of Claim 1, wherein said first pattern and said second pattern are connected to each other, thereby forming one continuous pattern.

11. (Original) The photomask of Claim 1, wherein said given distance is not larger than  $(\lambda/NA) \times M$ , wherein  $\lambda$  indicates a wavelength of the exposing light and M and NA respectively indicate a reduction ratio and numerical aperture of a reduction projection optical system of a projection aligner.

12. (Original) The photomask of Claim 1, wherein each of said first pattern and said second pattern has a width not larger than  $(0.8 \times \lambda/NA) \times M$ , wherein  $\lambda$  indicates a wavelength of

the exposing light and M and NA respectively indicate a reduction ratio and numerical aperture of a reduction projection optical system of a projection aligner.

13. (Original) The photomask of Claim 12, wherein a difference in the width between said first pattern and said second pattern is not larger than  $(0.2 \times \lambda/NA) \times M$ .

14. (Currently amended) The photomask of Claim 13, wherein a ratio of said first line width ~~the width of said phase shifter of the mask enhancer structure of said first pattern~~ to the width of said first pattern is smaller than a ratio of said second line width ~~the width of said phase shifter of the mask enhancer structure of said second pattern~~ to the width of said second pattern.

15. (Original) The photomask of Claim 1, wherein each of said first pattern and said second pattern is provided with a semi-shielding portion for partially transmitting the exposing light in an identical phase with respect to said transparent portion instead of said shielding portion of the mask enhancer structure.

16. (Original) The photomask of Claim 15, wherein said semi-shielding portion transmits the exposing light with a phase difference not less than  $(-30 + 360 \times n)$  degrees and not more than  $(30 + 360 \times n)$  degrees (wherein n is an integer) with respect to said transparent portion.

17. (Original) The photomask of Claim 15, wherein said semi-shielding portion is made of a metal thin film with a thickness of 30 nm or less.

18. (Original) The photomask of Claim 1, wherein said phase shifter of the mask enhancer structure of each of said first pattern and said second pattern transmits the exposing light with a phase difference not less than  $(150 + 360 \times n)$  degrees and not more than  $(210 + 360 \times n)$  degrees (wherein  $n$  is an integer) with respect to said transparent portion.

19. (Original) The photomask of Claim 1, wherein said phase shifter of the mask enhancer structure of each of said first pattern and said second pattern is formed by trenching said transparent substrate.

20-29. (Cancelled)

30. (New) The photomask of Claim 1, wherein said third pattern is another pattern separated from said first and second patterns.

31. (New) The photomask of Claim 1, wherein each of said first and second patterns has a length of  $2 \times \lambda \times M$  or more, wherein  $\lambda$  indicates a wavelength of the exposing light and  $M$  indicates a reduction ratio of a reduction projection optical system of a projection aligner.